

Surface wrinkling as a metrology tool

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Mechanical properties are critical in many applications

- predictive modeling of complex systems
- performance and reliability

Measuring mechanical properties of sub-micron (nano) films remains difficult



Nanomechanics

Indentation





clamped-free AFM cantilever



Rabe et al. *J Vac Sci Technol B* **15** 1506 (1997) Hurley et al. *J Appl Phys* **94** 2347 (2003)

В 400 Z-height (nm) 200 ₹ 1.5 2000-1.0 Z-height 5 0.5 1000 (nm) 5 1.0 X-position (µm) 1.5 0.5 20 - T Y-position (µm) 20 X-position (μm)

O'Connell and McKenna, Science 307, 1760-1763 (2005).



Raegan et al. Eur. Phys. J. E 19, 453-459 (2006).

Nanobubbles



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2.5-6.5 cm -----+ Modified PDMS. Heat PDMS: PDMS 1 cm Ti (5 nm), Au (50 deposit Ti, then Au nm) Glass Cool 🛨 1.5 μm 1) Remove from alass slide 2) Heat to 110°C and cool

Bowden et al. Nature 393, 146 (1998).



Volynskii et al. J. Appl. Polym. Sci. 72, 1267 (1999).



Bowden et al. Appl. Phys. Lett. 75, 2557 (1999).



Lacour, et al. Appl. Phys. Lett. 82, 2404 (2003).



Bending of an elastic layer on an elastic foundation:



Assume sinusoidal deflection of the coating:

$$z = A\sin\frac{2\pi x}{\lambda}$$

Minimize the compressive force in the coating:



M.A. Biot, *J. Applied Mechanics* **4**, A1 (1937). A.L. Volynskii *et al. J. Material Science* **25**, 547 (2000). R. Huang, *J. Mechanics and Physics of Solids* **53**, 63 (2005).





Governing Equations



$$\lambda_e = 2\pi h_f \left(\frac{\overline{E}_f}{3\overline{E}_s}\right)^{1/3}$$

$$A_e = h_f \left(\frac{\varepsilon}{\varepsilon_c} - 1\right)^{1/2}$$

where $\overline{E} = E/(1-v^2)$

Assumptions:

- thick substrate $(h_s \gg h_f)$
- soft substrate ($E_s \leftrightarrow E_f$)
- interface must be well-bonded.
- materials behave elastically





Governing Equations





Surface wrinkling





Huang, Hong, and Suo, J. Mech. Phys. Solids 53, 2101 (2005).



Chung and Stafford, unpublished data.



Metrology platform

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 $\overline{E}_{f} = 3\overline{E}_{s} \left(\frac{\lambda_{e}}{2\pi h_{f}}\right)^{s}$

How to ascertain wavelength?

Optical microscopy

Small angle light scattering





Stafford et al. Encyclopedia of Materials: Science and Technology Online Updates (2006).



Validation



Stafford et al. *Nat. Mater.* **3**, 545 (2004). Stafford et al. *Rev. Sci. Instrum.* **76**, 062207 (2005).



Inorganic materials

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• Films cast on polished salt plates to facilitate film transfer.

- Wrinkling metrology could measure films down to 100 nm; indentation could not.
- o Semiconductor industry needs $E_f > 4$ GPa to withstand CMP.

Stafford et al. Nat. Mater. 3, 545 (2004).





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- Observe dramatic decrease in E_f below 30 nm
- Data can be explained by a surface layer (h*=2 nm) with reduced modulus (almost rubbery).

$$\lambda_e = 2\pi h_f \left(\frac{\overline{E}_f'}{3\overline{E}_s}\right)^{1/3}$$

Stafford et al. *Macromolecules* **39**, 5095-5099 (2006). R. Huang et al. *J. Aerospace Eng.* **20**, 38-44 (2007).



Soft materials

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100 80. ΡI ΡI ¥ . PS E_f (MPa) 60 Sample 1 $\phi_{PS} = 0.30$ 40Sample 2 $\phi_{PS} = 0.44$ 20 0 Solution blended prior to spin-coating. 0.32 0.36 0.40 0.44 $\phi_{\rm PS}$

$$\lambda_e = 2\pi h_f \left(\frac{\overline{E}_f}{3\overline{E}_s}\right)^{1/3}$$

$$0.78 \mu m < \lambda_e < 2.0 \mu m$$

 $(h_f = 100 nm)$
 $7.8 \mu m < \lambda_e < 20.0 \mu m$
 $(h_f = 1 \mu m)$

$$\varepsilon_c = -\frac{1}{4} \left(\frac{3\overline{E}_s}{\overline{E}_f} \right)^{2/3}$$

$$0.024 < \varepsilon_c < 0.179$$



Employ a 'sensor' film of known modulus and thickness to report back the substrate modulus:





- Approach is most sensitive for Es < 2 MPa
- Thickness of sensor film is critical for measurement sensitivity



 \cdot Stress decays into the substrate on the order of a wavelength ($\lambda_{e}\!)$



Reverse metrology

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Wilder et al. Macromolecules 39, 4138-4143 (2006).





- Application to new materials
 - LbL assemblies
 - polymer brushes
- Extend metrology to new measurements
 - critical strain
 - viscoelastic wrinkling



Wrinkling of PEMs

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Nolte et al. *Macromolecules* **38**, 5367 (2005). Nolte et al. *Macromolecules* **39**, 4841 (2006).



Wrinkling of PEMs

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LbL assembly of polyelectrolytes directly on PDMS





Wrinkling of brushes





- thickness grows linearly with reaction time (t_p)
- comparable thickness on PDMS as silicon.



Wrinkling of brushes





H. Huang et al. in preparation (2007).



Wrinkling of brushes

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$$h_f = \frac{\lambda_e}{2\pi} \left(\frac{\overline{E}_f}{3\overline{E}_s}\right)^{-1/3}$$

Measure brush thickness via wrinkling!

- assume bulk modulus
- \cdot wavelength \rightarrow thickness



A macroscopic measurement (wavelength) can provide accurate measure of a property at the nanometer scale (thickness)

H. Huang et al. in preparation (2007).



Reversibility in wrinkled brushes



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Heating/cooling cycleRinse with solvent (DMF/methanol)





Critical strain

$$\lambda_e = 2\pi h_f \left(\frac{\overline{E}_f}{3\overline{E}_s}\right)^{1/3}$$

$$\varepsilon_{c} = -\frac{1}{4} \left(\frac{3\overline{E}_{s}}{\overline{E}_{f}} \right)^{2/3}$$

- thickness dependence (linear)
- modulus ratio to the 1/3

no thickness dependence
modulus ratio to the 2/3

o One way to detect critical strain (ε_c) is through OM or LS....



Measure the scattered intensity as a function of compressive strain.



Critical strain - LS

$$\lambda_e = 2\pi h_f \left(\frac{\overline{E}_f}{3\overline{E}_s}\right)^{1/3}$$

$$\varepsilon_{c} = -\frac{1}{4} \left(\frac{3\overline{E}_{s}}{\overline{E}_{f}} \right)^{2/3}$$

- thickness dependence (linear)
- modulus ratio to the 1/3

no thickness dependence
modulus ratio to the 2/3

o One way to detect critical strain (ε_c) is through OM or LS....



Stafford, et al. Encyclopedia of Materials: Science and Technology Online Updates (2006).









Harrison et al. Appl. Phys. Lett. 85, 4016 (2004).



Critical strain



$$I(\varepsilon) = \left(\frac{\pi(n-1)h_f}{d}\right)^2 \left(\frac{\varepsilon}{\varepsilon_c} - 1\right)$$

For small argument, $0 < x << \sqrt{2}$, $J_1(x) \rightarrow x/2$

The intensity of the first order diffracted beam follows the linear dependence on the applied strain when $\varepsilon < 1.25\varepsilon_c$.



Critical strain

$$\lambda_e = 2\pi h_f \left(\frac{\overline{E}_f}{3\overline{E}_s}\right)^{1/3}$$

$$\varepsilon_{c} = -\frac{1}{4} \left(\frac{3\overline{E}_{s}}{\overline{E}_{f}} \right)^{2/3}$$

- thickness dependence (linear)
- modulus ratio to the 1/3

no thickness dependence
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o One way to detect critical strain (ε_c) is through OM or LS....



wavenumber (~wavelength) $1^{\mbox{\scriptsize st}}$ order diffraction spot



Critical strain - PS/PDMS

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Critical strain

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$$A = h_f \sqrt{\frac{\varepsilon + \eta}{\varepsilon_c + \eta} - 1}$$

 η is a residual surface strain

R. Huang et al. J. Aero. Eng. 20, 38 (2007).



 $\varepsilon_c \sim 0.44\%$ (calculated)

 $\varepsilon_c \sim 0.83\%$ (measured)



Critical strain - pPS/PDMS



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* Moduli were determined using the wrinkling wavelength

Future Plans

** Residual strains were determined by taking the difference between the measured and calculated critical strains.

Critical strain/stress vs Film annealing time



Critical strain - wettability



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Chung et al. *Soft Matter* accepted (2007).



Thermal wrinkling





Chung and Stafford, unpublished data

temperature controlled chamber



Thermal wrinkling

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Access to temperature dependent properties







Viscoelastic wrinkling





The wavelength of the instability is <u>initially</u> selected by the magnitude of the compressive strain and the thickness of the Al layer.



The amplitude of the instability grows exponentially with time until it saturates at the rubber state.



R. Huang, J. Mech. Phys. Solids 53, 63-69 (2005).



Thermal (viscoelastic) wrinkling



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Yoo P.J. and Lee, H. H.Macromolecules 2005, 38, 2820-2831



Thermal (viscoelastic) wrinkling



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Real-time Scattering



Scattering From Surface Grating







Real-Time Surface Scattering

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Time, t



R. Huang, J. Mech. Phys. Solids 53, 63-69 (2005).



Scattering Data

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2500 Increase in amplitude 2000 Intensity (arb. units) Increase in wavelength 1500 $I \propto A^2$ $\Delta \mathbf{\dagger}$ 1000 500 Time (seconds) 50 150 200 2.65 2.60 2.55 2.60 2π Wavelength (µm) 2.50 **Q**_{max} 2.45 2.40 λ 2.45 2.35 2.30 2.40 10 ⁶810 Time (seconds) 4 6 8 1000 2 6 ż Time (seconds) 1000



Initial stage (constant wavelength, exponential growth in amplitude):





Wrinkling



• AFM results yield ~ 6.4 nm

Equilibrium wavelength:

$$\lambda_{eq} = 2\pi h_f \left[\frac{(1-2\nu)\mu_f H}{12(1-\nu)(1-\nu_f)\mu_R h_f} \right]^{1/4}$$
$$\mu_{\rm P} = 0.0931 MPa$$

<u>Critical stress:</u>

$$\sigma_{c} = -\sqrt{\frac{4(1-\nu)}{3(1-2\nu)(1-\nu_{f})}} \frac{h_{f}}{H} \mu_{f} \mu_{R}}$$

$$= 50.3 MPa$$

Equilibrium amplitude:

$$A_{eq} = h_f \sqrt{\frac{2}{3} \left(\frac{\sigma_0}{\sigma_c} - 1 \right)} = 8.19 \, n \, m$$







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